PRELIMINARY

SFF340

SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada,CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

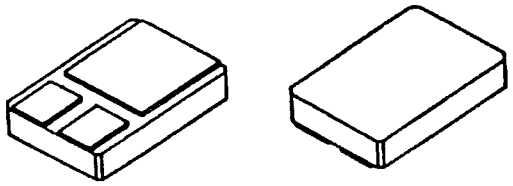
Designer's Data Sheet

10 AMP
400 VOLTS
0.55Ω
N-CHANNEL
POWER MOSFET

FEATURES:

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed surface mount power package
- TX, TXV and Space Level screening available
- Replaces: IRF340 Types

MILPACK



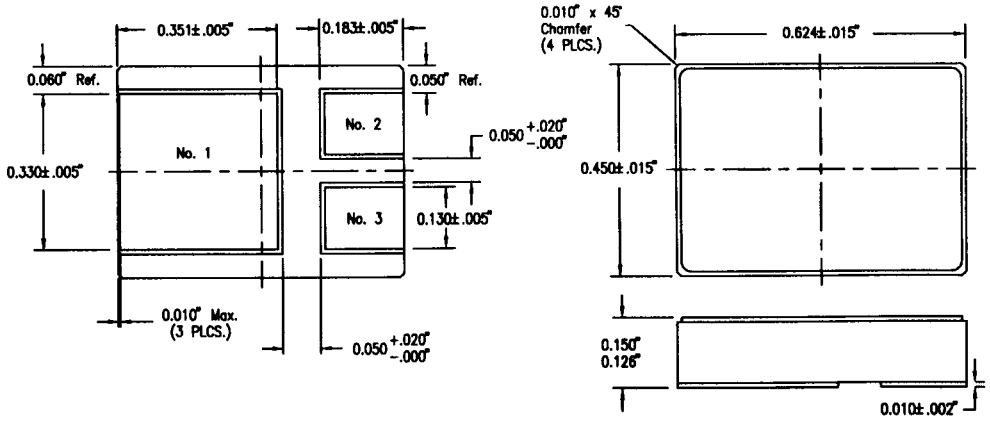
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V_{DS}	400	Volts
Gate to Source Voltage	V_{GS}	±20	Volts
Continuous Drain Current	I_D	10	Amps
Operating and Storage Temperature	T_{op} & T_{stg}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.7	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P_D	79 55	Watts

PACKAGE OUTLINE: MILPACK

PIN OUT:

PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.	DATA SHEET #: F00071 B	MED

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ELECTRICAL CHARACTERISTICS @ T_J=25 C (Unless Otherwise Specified)

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (VGS=0 V, ID=250μA)		BV_{DSS}	400	---	---	V
Drain to Source on State Resistance (VGS=10 V, ID=60% Rated ID		$R_{DS(on)}$	---	0.42	0.55	Ω
On State Drain Current (VDS >ID(on) X RDS(on) Max, VGS=10 V		$I_{D(on)}$	10	---	---	A
Gate Threshold Voltage (VDS=VGS, ID=250μA)		$V_{GS(th)}$	2.0	---	4.0	V
Forward Transconductance (VDS ≥ 50V, IDS=60% rated ID)		g_{fs}	5.8	8.7	---	S(℧)
Zero Gate Voltage Drain Current (VDS=max rated voltage, VGS=0 V) (VDS=80% rated VDS, VGS=0 V, TA=125°C)		I_{DSS}	--- ---	--- ---	250 1000	μA
Gate to Source Leakage Forward **Gate to Source Leakage Reverse**	At rated VGS	I_{GSS}	--- ---	--- ---	100 -100	nA
Total Gate Charge **Gate to Source Charge** **Gate to Drain Charge**	VGS=10 Volts 80% rated VDS ID=10A	Q_g Q_{gs} Q_{gd}	--- --- ---	43 6 22	65 9.3 33	nC
Turn on Delay Time **Rise Time** **Turn Off Delay Time** **Fall Time**	VDD=50% rated VDS ID=10A RG=9.1Ω RD=20Ω	$t_{d(on)}$ t_r $t_{d(off)}$ t_f	--- --- --- ---	14 27 50 24	9 30 74 36	nsec
Diode Forward Voltage (IS=rated ID, VGS=0 V, TJ=25°C)		V_{SD}	---	---	2.0	V
Diode Reverse Recovery Time **Reverse Recovery Charge**	TJ=25°C IF=rated ID di/dt=100 A/μsec	t_{rr} Q_{RR}	170 1.6	370 3.8	790 8.2	nsec μC
Input Capacitance **Output Capacitance** **Reverse Transfer Capacitance**	VGS=0 Volts VDS=25 Volts f= 1 MHz	C_{iss} C_{oss} C_{rss}	--- --- ---	1300 210 37	--- --- ---	pF

